

ABSTRACT

The active layer (active region) of the thin-film transistor making up the driver circuit is obtained by reformation implemented by scanning the continuous-wave laser light, condensed into a linear form or a rectangle form extremely longer in the longitudinal direction than in the transverse direction, along a given direction crossing the longitudinal direction. This is made up of a poly silicon film containing crystal grains having no grain boundaries crossing the direction of current flow, that is, a band-like polycrystalline silicon film. As a result, it is possible to implement a display device having stable and high quality active elements outside the display region on the insulating substrate.